

Abstract

Power transistor devices and techniques for reducing bowing in such devices are provided. In one aspect, a power transistor device is provided. The power transistor device
5 comprises a substrate, a device film formed on the substrate and an adhesion layer formed on a side of the substrate opposite the device film, wherein at least a portion of the adhesion layer is at least partially segmented. The power transistor device thereby exhibits a reduced amount of bowing relative to an amount of bowing expected without the segmenting of the adhesion layer. The power transistor device may be part of an integrated circuit.